

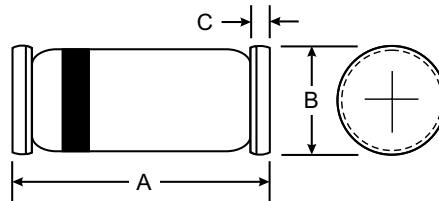

VOLTAGE RANGE: 20 V
CURRENT: 350mA

Features

- For general purpose applications
- These diodes feature very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.

Mechanical Data

- Case: SOD-80 (LL34), Glass
- Terminals: Solderable per MIL-STD-202,
- Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)



LL34/ SOD-80		
Dim	Min	Max
A	3.30	3.70
B	1.30	1.60
C	0.28	0.50

All Dimensions in mm

Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	20	V
Continuous Forward Current	I_F	350	mA
Repetitive Peak Forward Current at $t_p < 1\text{s}$,	I_{FRM}	1	A
Forward Surge Current at $t_p < 10\text{ ms}$,	I_{FSM}	7.5	A
Power Dissipation , $T_A = 65^\circ\text{C}$	P_D	330	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	300	$^\circ\text{C/W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Ambient Operating Temperature Range	T_a	-65 to + 125	$^\circ\text{C}$
Storage temperature range	T_s	-65 to + 150	$^\circ\text{C}$

Note: (1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature.

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 100\ \mu\text{A}$ (pulsed)	40	-	-	V
Reverse Current Pulse Test $t_p < 300\mu\text{s}$, $\delta < 2\%$	I_R	$V_R = 10\ \text{V}$	-	-	2	μA
		$V_R = 20\ \text{V}$	-	-	5	
		$V_R = 40\ \text{V}$	-	-	25	
Forward Voltage Pulse Test $t_p < 300\mu\text{s}$, $\delta < 2\%$	V_F	$I_F = 1\text{mA}$	-	-	0.30	V
		$I_F = 10\text{mA}$	-	-	0.40	
		$I_F = 30\text{mA}$	-	-	0.50	
		$I_F = 100\text{mA}$	-	-	0.75	
		$I_F = 500\text{mA}$	-	-	0.90	
Diode Capacitance	C_d	$V_R = 1\text{V}$, $f = 1\text{MHz}$	-	12	-	pF



RATING AND CHARACTERISTIC CURVES (LL47)

